

The documentation and process conversion measures necessary to comply with this revision shall be completed by 7 June 2014.

INCH-POUND

MIL-PRF-19500/556L  
7 March 2014  
SUPERSEDING  
MIL-PRF-19500/556K  
27 December 2010

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, FIELD EFFECT TRANSISTOR, N-CHANNEL, SILICON,  
TYPES 2N6782, 2N6782U, 2N6784, 2N6784U, 2N6786, AND 2N6786U,  
JAN, JANTX, JANTXV, JANS, JANHC, AND JANKC

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

1.1 Scope. This specification covers the performance requirements for an N-channel, enhancement-mode, MOSFET, power transistor. Four levels of product assurance are provided for each encapsulated device type as specified in [MIL-PRF-19500](#). Two levels of product assurance are provided for each unencapsulated device type.

1.2 Physical dimensions. See [figure 1](#) [similar to TO-205AF (formerly TO-39)], [figure 2](#) (LCC), and [figures 3](#) and [4](#) for JANHC and JANKC die dimensions.

1.3 Maximum ratings. Unless otherwise specified,  $T_A = +25^\circ\text{C}$ .

Type	$P_T$ (1) $T_C = +25^\circ\text{C}$	$P_T$ $T_A = +25^\circ\text{C}$	$V_{DS}$	$V_{DG}$	$V_{GS}$	$I_{D1}$ (2) (3) $T_C = +25^\circ\text{C}$	$I_{D2}$ (2) $T_C = +100^\circ\text{C}$	$I_S$	$I_{DM}$ (4)	$T_J$ and $T_{STG}$	$V_{ISO}$ 70,000 foot altitude
	<u>W</u>	<u>W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A(pk)</u>	<u>°C</u>	<u>V dc</u>
2N6782, U	15	0.8	100	100	$\pm 20$	3.5	2.25	3.50	14.0	-55 to	
2N6784, U	15	0.8	200	200	$\pm 20$	2.25	1.50	2.25	9.0	+150	
2N6786, U	15	0.8	400	400	$\pm 20$	1.25	0.80	1.25	5.5		400

(1) Derate linearly 0.12 W/°C for  $T_C > +25^\circ\text{C}$ .

(2) The following formula derives the maximum theoretical  $I_D$  limit.  $I_D$  is limited by package and internal wires and may be limited by pin diameter:

$$I_D = \sqrt{\frac{T_{JM} - T_C}{(R_{\theta IC}) \times (R_{DS(on)} \text{ at } T_{JM})}}$$

(3) See [figure 5](#), maximum drain current graph.

(4)  $I_{DM} = 4 \times I_{D1}$  as calculated in note 2.

\* Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to [Semiconductor@dla.mil](mailto:Semiconductor@dla.mil). Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil/>.

1.4 Primary electrical characteristics at  $T_C = +25^\circ\text{C}$ .

Type	Min $V_{(BR)DSS}$ $V_{GS} = 0$ $I_D = 1.0$ mA dc	$V_{GS(TH)}$ $V_{DS} \geq V_{GS}$ $I_D = 0.25$ mA dc		Max $I_{DSS1}$ $V_{GS} = 0$ $V_{DS} = 80$ percent of rated $V_{DS}$	Max $r_{DS(ON)}$ (1) $V_{GS} = 10$ V dc		$R_{\theta JC}$ max  (2)
					$T_J = +25^\circ\text{C}$ at $I_{D2}$	$T_J = +150^\circ\text{C}$ at $I_{D2}$	
	V dc	V dc		$\mu\text{A dc}$	ohm	ohm	$^\circ\text{C/W}$
		Min	Max				
2N6782, U	100	2.0	4.0	25	0.60	1.20	8.33
2N6784, U	200	2.0	4.0	25	1.50	3.15	8.33
2N6786, U	400	2.0	4.0	25	3.60	9.00	8.33

(1) Pulsed (see 4.5.1).

(2) See figure 6, thermal impedance curves.

## 2. APPLICABLE DOCUMENTS

\* 2.1 General. The documents listed in this section are specified in sections 3 or 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3 or 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

## DEPARTMENT OF DEFENSE SPECIFICATIONS

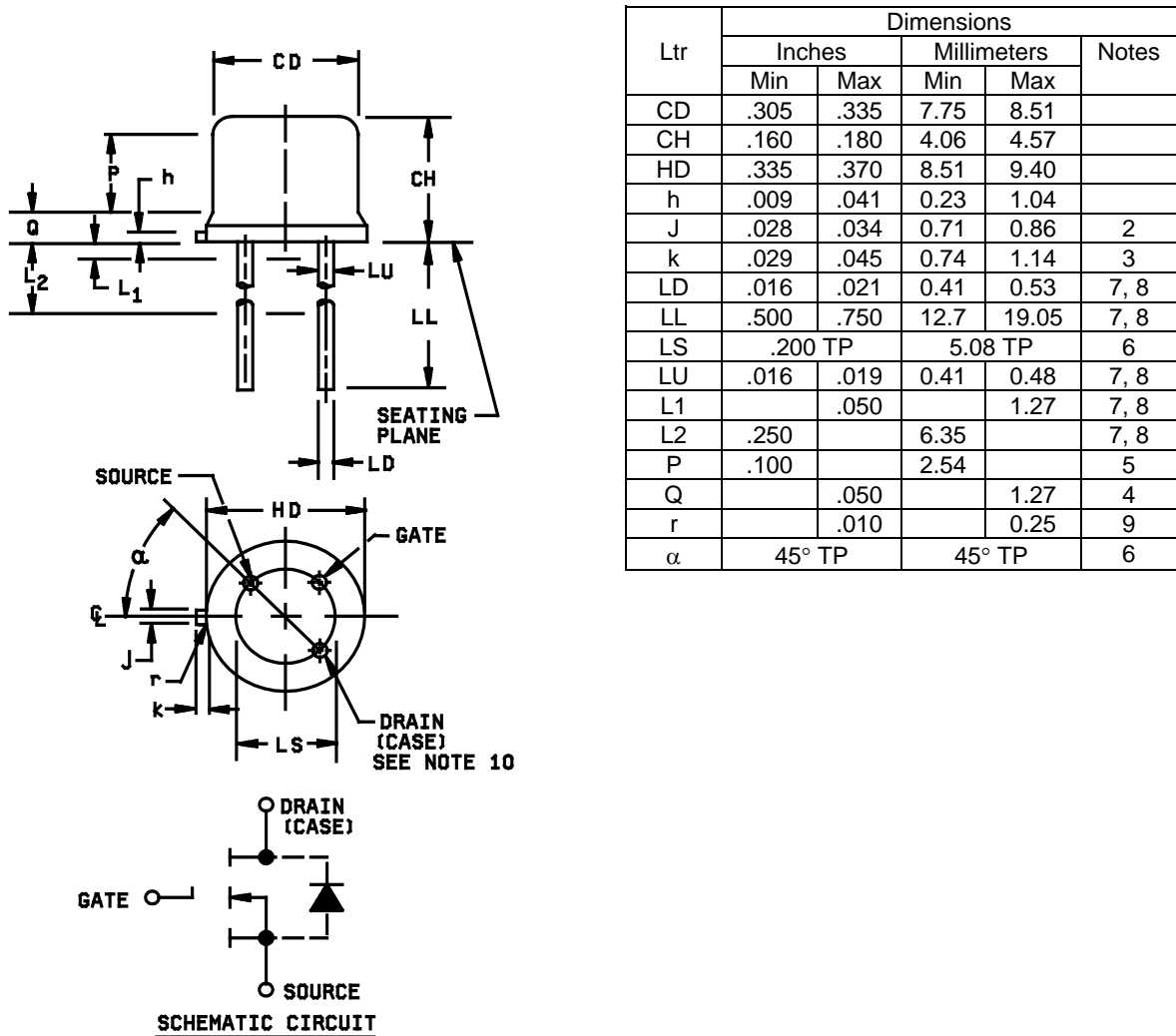
[MIL-PRF-19500](#) - Semiconductor Devices, General Specification for.

## DEPARTMENT OF DEFENSE STANDARDS

[MIL-STD-750](#) - Test Methods for Semiconductor Devices.

\* (Copies of these documents are available online at <http://quicksearch.dla.mil/>).

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

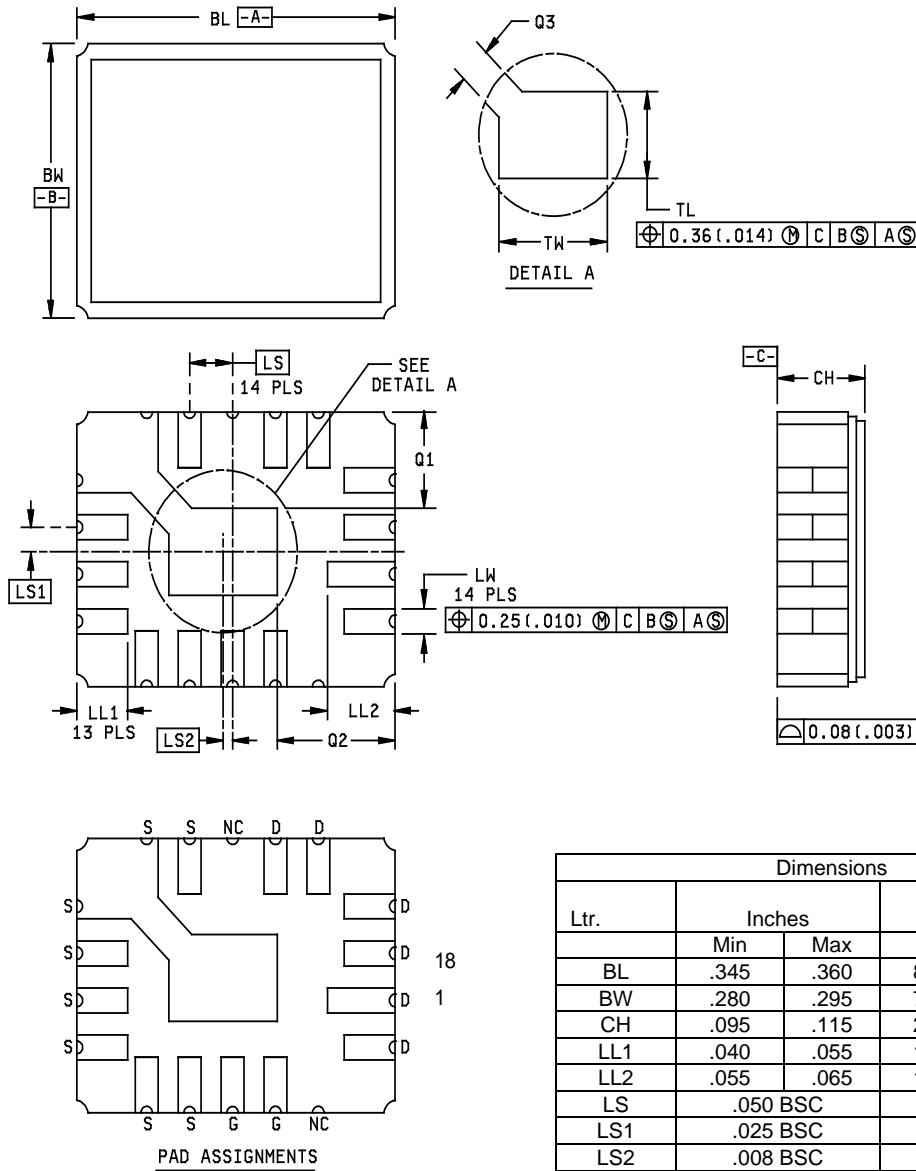


NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Beyond radius (r) maximum, J shall be held for a minimum length of .011 (0.28 mm).
3. Dimension k measured from maximum HD.
4. Outline in this zone is not controlled.
5. Dimension CD shall not vary more than .010 (0.25 mm) in zone P. This zone is controlled for automatic handling.
6. Leads at gauge plane .054 +.001, -.000 (1.37 +0.03, -0.00 mm) below seating plane shall be within .007 (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
7. LU applies between L<sub>1</sub> and L<sub>2</sub>. LD applies between L<sub>2</sub> and L minimum. Diameter is uncontrolled in L<sub>1</sub> and beyond LL minimum.
8. All three leads.
9. Radius (r) applies to both inside corners of tab.
10. Drain is electrically connected to the case.
11. In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.

FIGURE 1. Physical dimensions for TO-205AF.

MIL-PRF-19500/556L



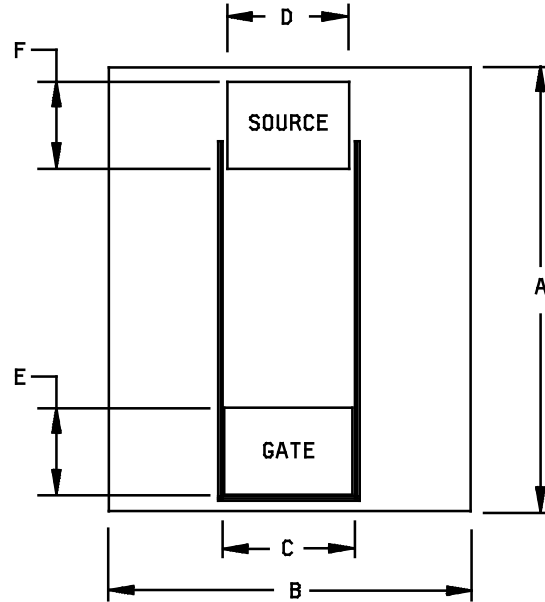
Dimensions				
Ltr.	Inches		Millimeters	
	Min	Max	Min	Max
BL	.345	.360	8.76	9.14
BW	.280	.295	7.11	7.49
CH	.095	.115	2.41	2.92
LL1	.040	.055	1.02	1.40
LL2	.055	.065	1.40	1.65
LS	.050 BSC		1.27 BSC	
LS1	.025 BSC		0.635 BSC	
LS2	.008 BSC		0.203 BSC	
LW	.020	.030	0.51	0.76
Q1	.105 REF		2.67 REF	
Q2	.120 REF		3.05 REF	
Q3	.045	.055	1.14	1.40
TL	.070	.080	1.78	2.03
TW	.120	.130	3.05	3.30

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi$ x symbology.
4. Ceramic package only.

FIGURE 2. Physical dimensions for LCC.

2N6782, 2N6784, and 2N6786



Ltr	Dimensions - 2N6782				Dimensions - 2N6784				Dimensions - 2N6786			
	Inches		Millimeters		Inches		Millimeters		Inches		Millimeters	
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
A	0.082	0.092	2.08	2.34	0.082	0.092	2.08	2.34	0.101	0.111	2.55	2.81
B	0.059	0.069	1.48	1.74	0.062	0.072	1.57	1.83	0.071	0.081	1.81	2.07
C	0.021	0.031	0.53	0.79	0.020	0.030	0.50	0.76	0.020	0.030	0.50	0.76
D	0.020	0.030	0.50	0.76	0.019	0.029	0.47	0.73	0.019	0.029	0.47	0.73
E	0.013	0.023	0.32	0.58	0.012	0.022	0.31	0.57	0.012	0.022	0.31	0.57
F	0.014	0.024	0.34	0.60	0.013	0.023	0.32	0.58	0.013	0.023	0.32	0.58

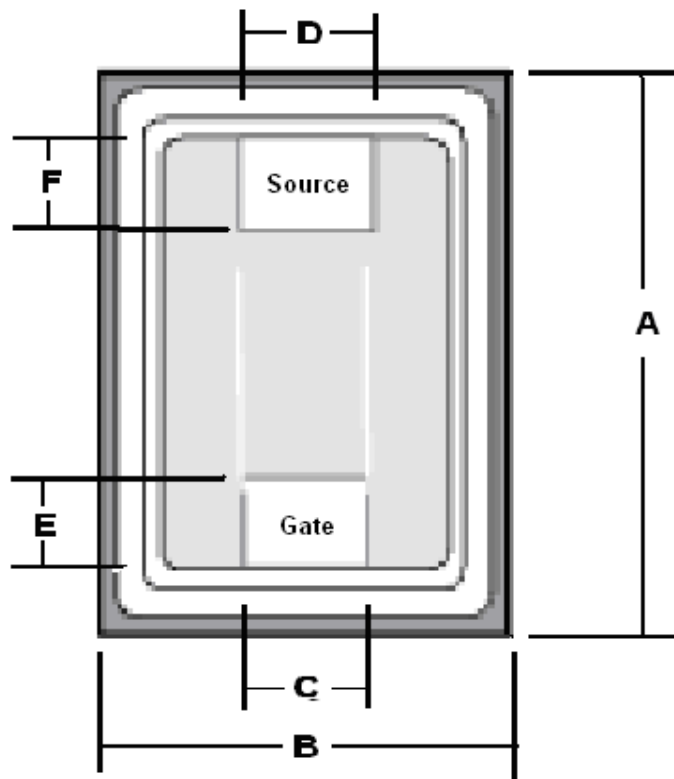
NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Unless otherwise specified, tolerance is  $\pm 0.005$  inch (0.13 mm).
4. The physical characteristics of the die are: The back metals are chromium, nickel, and silver and the back contact is the drain. The top metal is aluminum.
5. Die thickness is .0187 inch (0.475 mm)  $\pm 0.0050$  inch (0.130 mm).

FIGURE 3. JANHCA and JANKCA die dimensions.

MIL-PRF-19500/556L

2N6782 and 2N6784



Ltr	Dimensions - 2N6782 and 2N6784			
	Inches		Millimeters	
	Min	Max	Min	Max
A	.082	.089	2.08	2.26
B	.062	.066	1.58	1.68
C	.019	.021	0.48	0.53
D	.022	.024	0.56	0.61
E	.012	.014	0.30	0.36
F	.013	.015	0.33	0.38

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Unless otherwise specified, tolerance is  $\pm 0.005$  inch (0.13 mm).
4. The physical characteristics of the die are: The back metals are chromium, nickel, and silver and the back contact is the drain. The top metal is aluminum.
5. Die thickness is .015 inch (0.38 mm)  $\pm 0.001$  inch (0.025 mm).

FIGURE 4. JANHCB and JANKCB die dimensions (2N6782, 2N6784).

### 3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in [MIL-PRF-19500](#) and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see [4.2](#) and [6.3](#)).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in [MIL-PRF-19500](#) and as follows.

nC ----- nano coulomb.

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in [MIL-PRF-19500](#) and on [figures 1](#) (TO-205), [2](#) (LCC), and [3](#) and [4](#) (die) herein.

3.4.1 Lead finish. Lead finish shall be solderable in accordance with [MIL-PRF-19500](#), [MIL-STD-750](#), and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see [6.2](#)).

3.4.2 Internal construction. Multiple chip construction shall not be permitted.

3.5 Marking. Marking shall be in accordance with [MIL-PRF-19500](#).

3.6 Electrostatic discharge protection. The devices covered by this specification require electrostatic protection.

3.6.1 Handling. MOS devices must be handled with certain precautions to avoid damage due to the accumulation of static charge. However, the following handling practices are recommended (see [3.6](#)).

- a. Devices should be handled on benches with conductive handling devices.
- b. Ground test equipment, tools, and personnel handling devices.
- c. Do not handle devices by the leads.
- d. Store devices in conductive foam or carriers.
- e. Avoid use of plastic, rubber, or silk in MOS areas.
- f. Maintain relative humidity above 50 percent if practical.
- g. Care should be exercised during test and troubleshooting to apply not more than maximum rated voltage to any lead.
- h. Gate must be terminated to source,  $R \leq 100 \text{ k}\Omega$ , whenever bias voltage is to be applied drain to source.

3.7 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in [1.3](#), [1.4](#), and [table I](#).

3.8 Electrical test requirements. The electrical test requirements shall be as specified in [table I](#).

3.9 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

#### 4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of table II tests, the tests specified in table II herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

4.2.2 JANHC and JANKC die. Qualification shall be in accordance with MIL-PRF-19500.



4.3 Screening (JANS, JANTX and JANTXV levels only). Screening shall be in accordance with table E-IV of MIL-PRF-19500 and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table E-IV of MIL-PRF-19500) (1) (2)	Measurement	
	JANS level	JANTX and JANTXV levels
(3)	Gate stress test (see 4.3.1).	Gate stress test (see 4.3.1).
(3) (4)	Unclamped inductive switching, method 3470 of MIL-STD-750 (see 4.3.2), optional.	Unclamped inductive switching, method 3470 of MIL-STD-750 (see 4.3.2), optional.
(3) 3c	Method 3161 of MIL-STD-750 (see 4.3.3).	Method 3161 of MIL-STD-750 (see 4.3.3).
9	$I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ , subgroup 2 of table I herein.	Not applicable.
10	Method 1042 of MIL-STD-750, test condition B.	Method 1042 of MIL-STD-750, test condition B.
11	$I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ , $r_{DS(on)1}$ , $V_{GS(TH)1}$ , Subgroup 2 of table I herein; $\Delta I_{GSSF1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 25$ $\mu$ A dc or $\pm 100$ percent of initial value, whichever is greater.	$I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ , $r_{DS(on)1}$ , $V_{GS(TH)1}$ Subgroup 2 of table I herein.
12	Method 1042 of MIL-STD-750, test condition A, $t = 240$ hours.	Method 1042 of MIL-STD-750, test condition A.
13	Subgroups 2 and 3 of table I herein; $\Delta I_{GSSF1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 25$ $\mu$ A dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta r_{DS(on)1} = \pm 20$ percent of initial value. $\Delta V_{GS(TH)1} = \pm 20$ percent of initial value.	Subgroup 2 of table I herein; $\Delta I_{GSSF1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 25$ $\mu$ A dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta r_{DS(on)1} = \pm 20$ percent of initial value. $\Delta V_{GS(TH)1} = \pm 20$ percent of initial value.

- (1) At the end of the test program,  $I_{GSSF1}$ ,  $I_{GSSR1}$ , and  $I_{DSS1}$  are measured.
- (2) An out-of-family program to characterize  $I_{GSSF1}$ ,  $I_{GSSR1}$ ,  $I_{DSS1}$ , and  $V_{GS(th)1}$  shall be invoked.
- (3) Shall be performed anytime after temperature cycling, screen 3a; and does not need to be repeated in screening requirements.
- (4) This test is optional in screening if performed in table I, subgroup 5.

4.3.1 Gate stress test. Apply  $V_{GS} = \pm 30$  V minimum for  $t = 250$   $\mu$ s minimum.

\* 4.3.2 Unclamped inductive switching.

- a. Peak current ( $I_D$ )..... rated  $I_{D1}$ .
- b. Peak gate voltage ( $V_{GS}$ ) ..... 10 V.
- c. Gate to source resistor ( $R_{GS}$ ).....  $25 \Omega \leq R_{GS} \leq 200 \Omega$ .
- d. Initial case temperature ( $T_C$ ).....  $+25^\circ\text{C} +10^\circ\text{C}, -5^\circ\text{C}$ .
- \* e. Inductance (L) ..... 100  $\mu$ H minimum.
- f. Number of pulses to be applied ..... 1 pulse minimum.
- g. Pulse repetition rate ..... None.

4.3.3 Thermal impedance. The thermal impedance measurements shall be performed in accordance with method 3161 of MIL-STD-750 using the guidelines in that method for determining  $I_M$ ,  $I_H$ ,  $t_H$ ,  $t_{SW}$ , (and  $V_H$  where appropriate). Measurement delay time ( $t_{MD}$ ) = 70  $\mu$ s max. See table II, group E, subgroup 4 herein.

4.3.4 Screening (JANHC and JANKC). Screening of die shall be in accordance with MIL-PRF-19500. As a minimum, die shall be 100-percent probed in accordance with table I, subgroup 2, except test current shall not exceed 20 A.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500. Alternate flow is allowed for quality conformance inspection in accordance with MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500 and table I herein. Electrical measurements (end-points) shall be in accordance with the inspections of table I, subgroup 2 herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VIA (JANS) and table E-VIB (JAN, JANTX, and JANTXV) of MIL-PRF-19500 and herein. Electrical measurements (end-points) shall be in accordance with the inspections of table I, subgroup 2 herein.

\* 4.4.2.1 Group B inspection, table E-VIA (JANS) of MIL-PRF-19500.

Subgroup	Method	Condition
B3	1051	Test condition G.
* B4	1042	Intermittent operation life, test condition D. The heating cycle shall be 1 minute minimum.
B5	1042	Accelerated steady-state operation life; test condition A, $V_{DS} = \text{rated}$ , $T_A = +175^\circ\text{C}$ , $t = 120$ hours. Read and record $V_{(BR)DSS}$ (pre and post) at $1 \text{ mA} = I_D$ . Read and record $I_{DSS}$ (pre and post). Deltas for $V_{(BR)DSS}$ shall not exceed 10 percent and $I_{DSS}$ shall not exceed 25 $\mu$ A.  Accelerated steady-state gate bias; condition B, $V_{GS} = \text{rated}$ , $T_A = +175^\circ\text{C}$ , $t = 24$ hours.
B5	2037	Bond strength; test condition D.

\* 4.4.2.2 Group B inspection, table E-VIB (JAN, JANTX, and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B2	1051	Test condition G.
* B3	1042	Intermittent operation life, test condition D. The heating cycle shall be 1 minute minimum.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VII of [MIL-PRF-19500](#) and as follows. Electrical measurements (end-points) shall be in accordance with the inspections of [table I](#), subgroup 2 herein.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C2	2036	Test condition E (Not required for LCC).
C5	3161	See 4.5.2, $R_{\theta JC(max)} = 8.33^{\circ}C/W$ .
C6	1042	Intermittent operation life, test condition D, 6,000 cycles. The heating cycle shall be 1 minute minimum.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-IX of [MIL-PRF-19500](#) and as specified in [table II](#) herein. Electrical measurements (end-points) shall be in accordance with [table I](#), subgroup 2 herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of [MIL-STD-750](#).

4.5.2 Thermal resistance. The thermal resistance measurements shall be performed in accordance with method 3161 of [MIL-STD-750](#) using the guidelines in that method for determining  $I_M$ ,  $I_H$ ,  $t_H$ ,  $t_{SW}$  (and  $V_H$  where appropriate). Measurement delay time ( $t_{MD}$ ) = 70  $\mu$ s max. See [table II](#), group E, subgroup 4 herein.

## MIL-PRF-19500/556L

TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Thermal impedance <u>2/</u>	3161	See 4.3.3	$Z_{\theta JC}$			$^{\circ}C/W$
Breakdown voltage, drain to source 2N6782, 2N6782U 2N6784, 2N6784U 2N6786, 2N6786U	3407	$V_{GS} = 0$ V dc, $I_D = 1.0$ mA dc, bias condition C	$V_{(BR)DSS}$	100 200 400		V dc V dc V dc
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$ , $I_D = 0.25$ mA dc	$V_{GS(TH)1}$	2.0	4.0	V dc
Gate current	3411	$V_{GS} = +20$ V dc, bias condition C, $V_{DS} = 0$	$I_{GSSF1}$		+100	nA dc
Gate current	3411	$V_{GS} = -20$ V dc, bias condition C, $V_{DS} = 0$	$I_{GSSR1}$		-100	nA dc
Drain current	3413	$V_{GS} = 0$ V dc, bias condition C, $V_{DS} = 80$ percent of rated $V_{DS}$	$I_{DSS1}$		25	$\mu A$ dc
Static drain to source on-state resistance 2N6782, 2N6782U 2N6784, 2N6784U 2N6786, 2N6786U	3421	$V_{GS} = 10$ V dc, condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(on)1}$		0.60 1.50 3.60	ohm ohm ohm
Static drain to source on-state resistance 2N6782, 2N6782U 2N6784, 2N6784U 2N6786, 2N6786U	3421	$V_{GS} = 10$ V dc, condition A, pulsed (see 4.5.1), $I_D = I_{D1}$	$r_{DS(on)2}$		0.61 1.60 3.70	ohm ohm ohm
Forward voltage (source drain diode) 2N6782, 2N6782U 2N6784, 2N6784U 2N6786, 2N6786U	4011	Pulsed (see 4.5.1), $I_D = I_{D1}$ , $V_{GS} = 0$ V dc	$V_{SD}$		1.5 1.5 1.4	V V V

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection 1/	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 3</u>						
High-temperature operation:						
Gate current	3411	$T_C = T_J = +125^\circ\text{C}$ $V_{GS} = +20\text{ V dc and } -20\text{ V dc,}$ bias condition C, $V_{DS} = 0$	$I_{GSS2}$		$\pm 200$	nA dc
Drain current	3413	$V_{GS} = 0\text{ V dc, bias condition C,}$ $V_{DS} = 80\text{ percent of rated } V_{DS}$	$I_{DSS2}$		0.25	mA dc
Gate to source voltage (thresholds)	3403	$V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA dc}$	$V_{GS(TH)2}$	1.0		V dc
Static drain to source on-state resistance	3421	$V_{GS} = 10\text{ V dc, pulsed (see 4.5.1),}$ $I_D = I_{D2}$	$r_{DS(on)3}$			
					1.08	ohm
					2.81	ohm
					7.92	ohm
Low-temperature operation:						
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA dc}$	$V_{GS(TH)3}$		5.0	V dc
<u>Subgroup 4</u>						
Switching time test	3472	$I_D = I_{D1}, V_{GS} = 10\text{ V dc,}$ $R_G = 7.5\Omega, V_{DD} = 50\text{ percent}$ of rated $V_{DS}$				
Turn-on delay time			$t_{d(on)}$			
					15	ns
					15	ns
					15	ns

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 4</u> - Continued						
Rise time			$t_r$			
2N6782, 2N6782U					25	ns
2N6784, 2N6784U					20	ns
2N6786, 2N6786U					20	ns
Turn-off delay time			$t_{d(off)}$			
2N6782, 2N6782U					25	ns
2N6784, 2N6784U					30	ns
2N6786, 2N6786U					35	ns
Fall time			$t_f$			
2N6782, 2N6782U					20	ns
2N6784, 2N6784U					20	ns
2N6786, 2N6786U					30	ns
<u>Subgroup 5</u>						
Single pulse unclamped Inductive switching <u>3/</u>	3470	See <a href="#">4.3.2</a>				
Safe operating area test	3474	See <a href="#">figure 7</a> ; $t_p = 10$ ms minimum, $V_{DS} = 80$ percent of maximum rated $V_{DS}$ , ( $V_{DS} \leq$ 200)				
Electrical measurements		See <a href="#">table I</a> , subgroup 2 herein.				
<u>Subgroup 6</u>						
Not applicable						
<u>Subgroup 7</u>						
Gate charge	3471	Condition B				
<u>Test 1</u>						
On-state gate charge			$Q_{g(on)}$			
2N6782, 2N6782U					8.1	nC
2N6784, 2N6784U					8.6	nC
2N6786, 2N6786U					12	nC

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 7</u> - Continued						
<u>Test 2</u>						
Gate to source charge			$Q_{gs}$			
2N6782, 2N6782U					1.7	nC
2N6784, 2N6784U					1.5	nC
2N6786, 2N6786U					1.8	nC
<u>Test 3</u>						
Gate to drain charge			$Q_{gd}$			
2N6782, 2N6782U					4.5	nC
2N6784, 2N6784U					5.5	nC
2N6786, 2N6786U					7.6	nC
Reverse recovery time	3473	$d_i/d_t \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq 50 \text{ V}$ , $I_D = I_{D1}$	$t_{rr}$			
2N6782, 2N6782U		$I_F = 3.5 \text{ A}$			180	ns
2N6784, 2N6784U		$I_F = 2.25 \text{ A}$			350	ns
2N6786, 2N6786U		$I_F = 1.25 \text{ A}$			540	ns

1/ For sampling plan, see [MIL-PRF-19500](#).

2/ This test required for the following end-point measurements only:

Group B, subgroups 2 and 3 (JANTXV).

Group B, subgroups 3 and 4 (JANS).

Group C, subgroup 2 and 6.

Group E, subgroup 1.

3/ This test is optional if performed as a 100 percent screen.

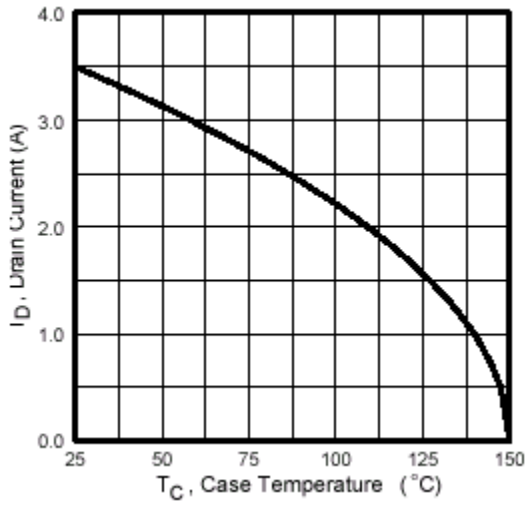
\* TABLE II. Group E inspection (all quality levels) for qualification or re-qualification only.

Inspection <u>1/</u>	MIL-STD-750		Sample plan
	Method	Conditions	
<u>Subgroup 1</u>			45 devices c = 0
Temperature cycling	1051	Test condition G, 500 cycles	
Hermetic seal	1071		
Fine leak			
Gross leak			
Electrical measurements		See <a href="#">table I</a> , subgroup 2	
<u>Subgroup 2 <u>2/</u></u>			45 devices c = 0
Steady-state reverse bias	1042	Condition A, 1,000 hours	
Electrical measurements		See <a href="#">table I</a> , subgroup 2	
Steady-state gate bias	1042	Condition B, 1,000 hours	
Electrical measurements		See <a href="#">table I</a> , subgroup 2	
<u>Subgroup 4</u>			Sample size N/A
Thermal impedance curves		See <a href="#">MIL-PRF-19500</a> .	
<u>Subgroup 5</u>			3 devices c = 0
* Barometric pressure	1001	Condition C, 2N6786 and 2N6786U only	
<u>Subgroup 10</u>			22 devices c = 0
Commutating diode for safe operating area test procedure for measuring dv/dt during reverse recovery of power MOSFET transistors or insulated gate bipolar transistors	3476	Test conditions shall be derived by the manufacturer.	

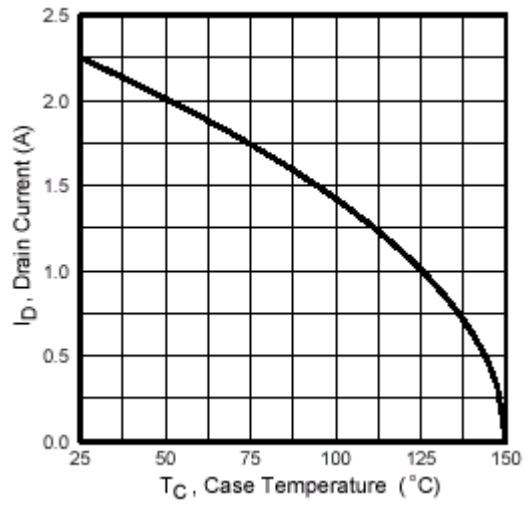
1/ JANHC and JANKC devices are qualified in accordance with [MIL-PRF-19500](#).

2/ A separate sample may be pulled for each test.

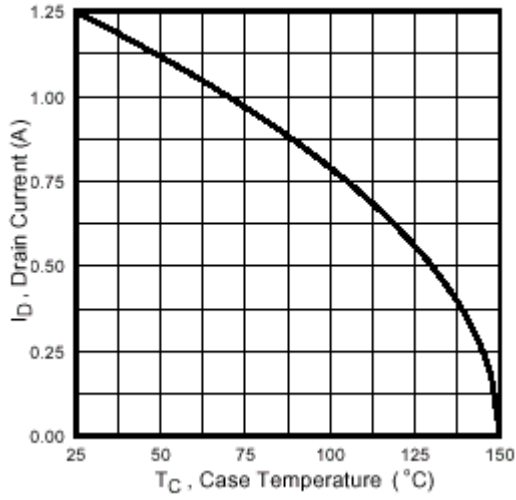




2N6782, 2N6782U



2N6784, 2N6784U



2N6786, 2N6786U

FIGURE 5. Maximum drain current versus case temperature graphs.

2N6782, 2N6782U, 2N6784, 2N6784U, 2N6786, 2N6786U

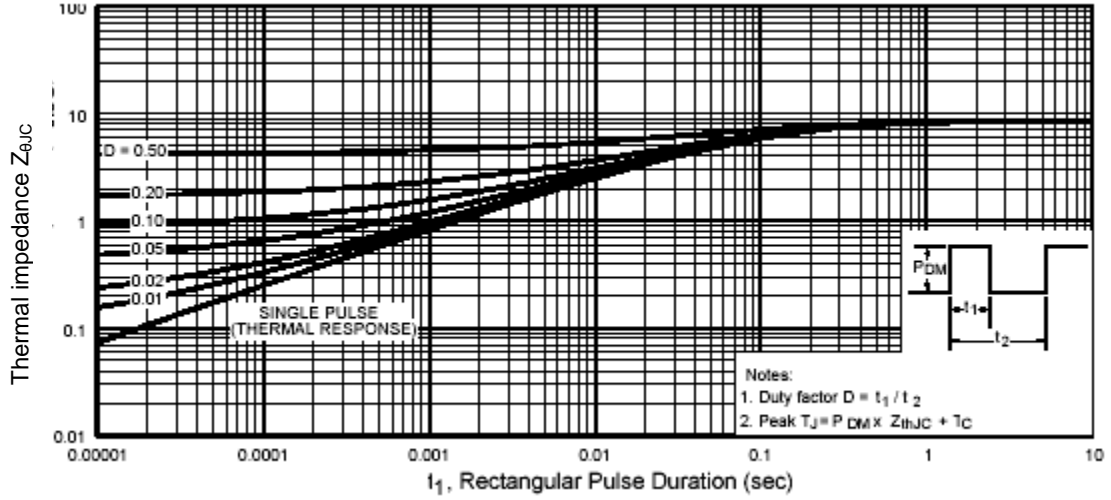


FIGURE 6. Thermal impedance curve.

2N6782, 2N6782U

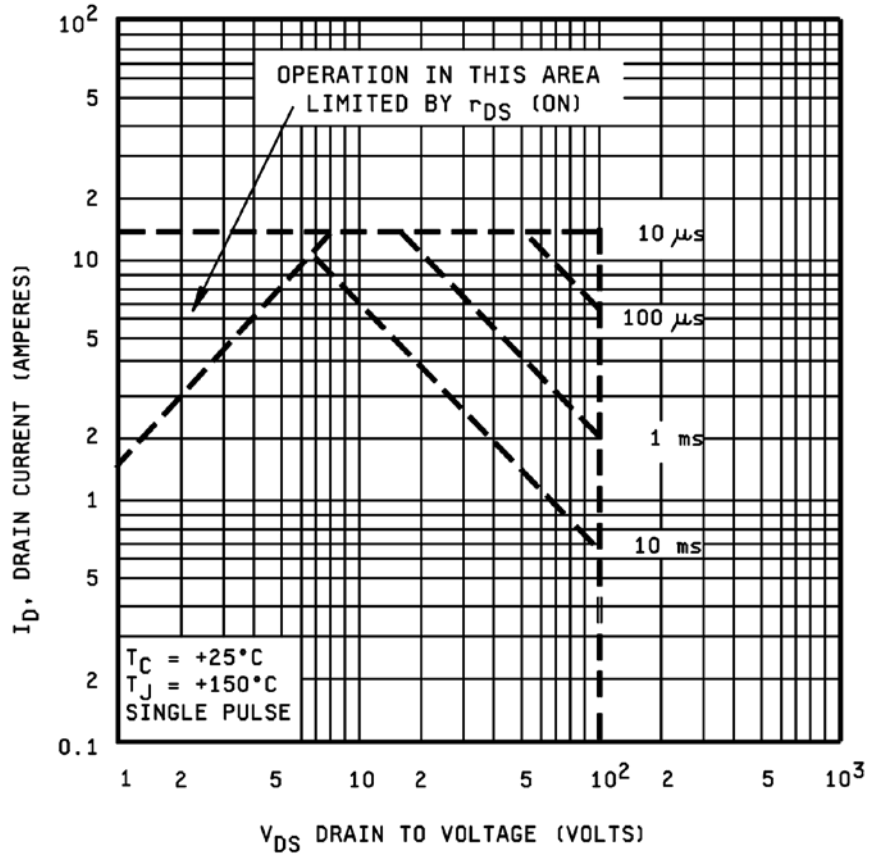
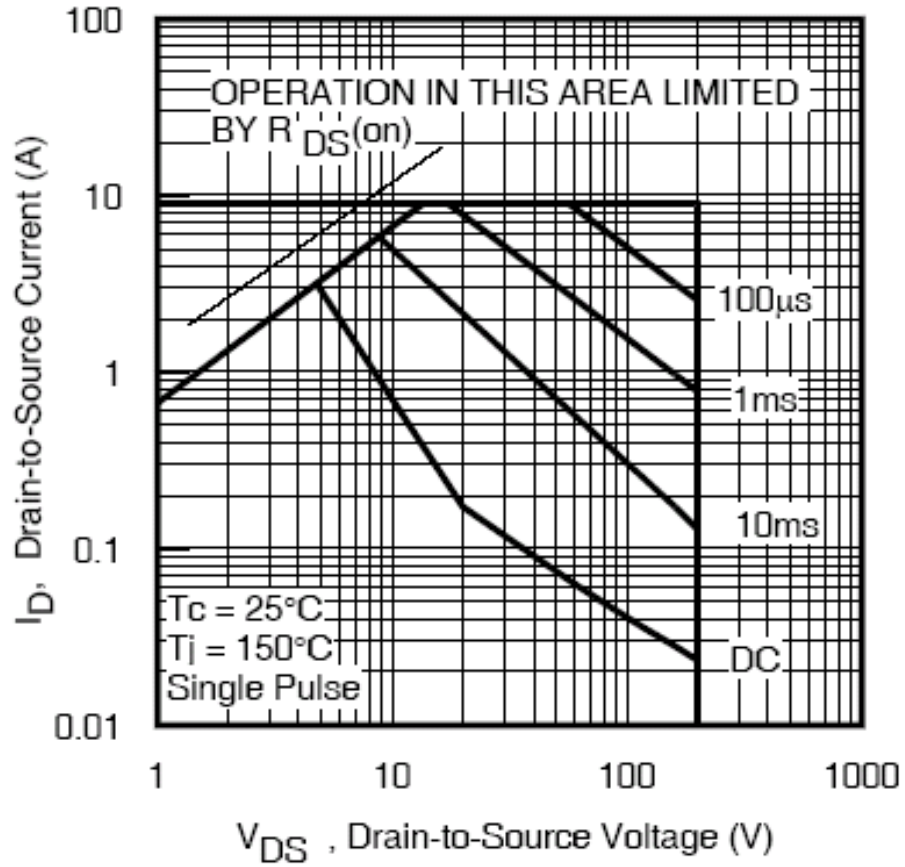
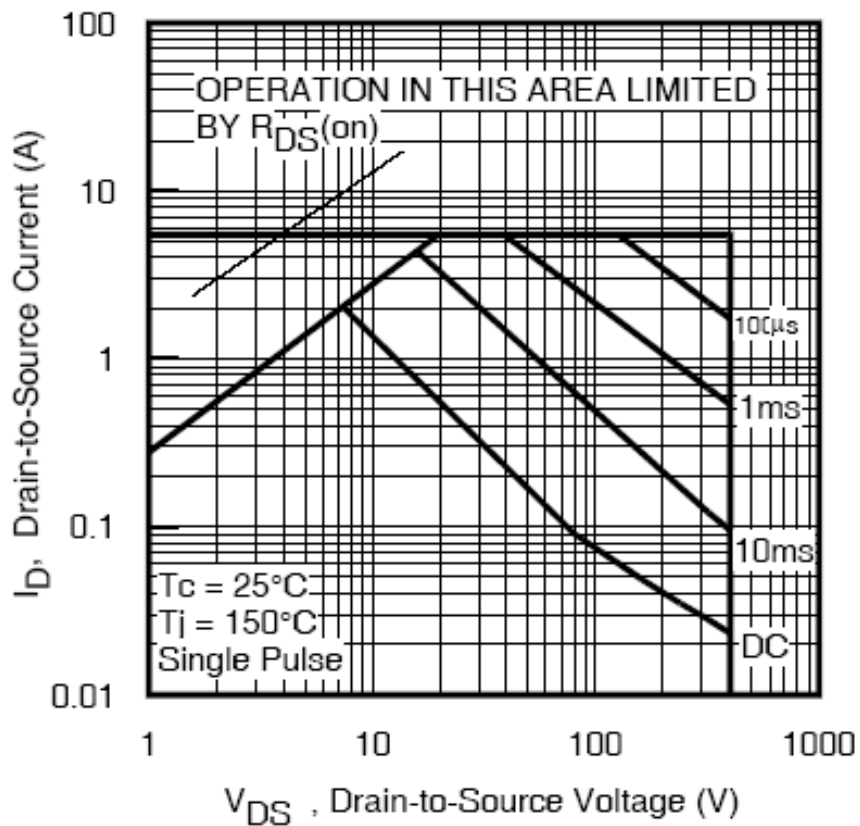


FIGURE 7. Maximum safe operating area.



\* FIGURE 7. Maximum safe operating area - Continued.

2N6786, 2N6786U



\* FIGURE 7. Maximum safe operating area - Continued.

## 5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

## 6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in [MIL-PRF-19500](#) are applicable to this specification.)

6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

\* 6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.1).
- \* d. The complete Part or Identifying Number (PIN), see title and section 1.
- e. For die acquisition, the JANHC or JANKC letter version shall be specified (see [figures 3 and 4](#)).

\* 6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List ([QML 19500](#)) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA Land and Maritime, ATTN: VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail [vqe.chief@dla.mil](mailto:vqe.chief@dla.mil). An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.dla.mil>.

6.4 Cross-reference and complement list. Parts from this specification may be used to replace the following commercial Part or Identifying Number (PIN). The term PIN is equivalent to the term part number which was previously used in this specification.

Preferred types	Commercial types
2N6782	IRFF110, IRFF111, IRFF112, IRFF113
2N6784	IRFF210, IRFF211, IRFF212, IRFF213
2N6786	IRFF310, IRFF311, IRFF312, IRFF313
2N6782U	IRFE110, IRFE111, IRFE112, IRFE113
2N6784U	IRFE210, IRFE211, IRFE212, IRFE213
2N6786U	IRFE310, IRFE311, IRFE312, IRFE313

6.5 Suppliers of JANHC and JANKC die. The qualified die suppliers with the applicable letter version (example, JANHCA2N6786) will be identified on the QML.

JANC ordering information		
PIN	Manufacturer	
	69210	43611
2N6782	JANHCA2N6782 JANKCA2N6782	JANHCB2N6782 JANKCB2N6782
2N6784	JANHCA2N6784 JANKCA2N6784	JANHCB2N6784 JANKCB2N6784
2N6786	JANHCA2N6786 JANKCA2N6786	

6.6 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the previous issue.

Custodians:  
 Army - CR  
 Navy - EC  
 Air Force - 85  
 DLA - CC

Preparing activity:  
 DLA - CC  
 (Project 5961-2014-056)

Review activities:  
 Army - AR, MI, SM  
 Navy - AS, MC  
 Air Force - 19

\* NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil/>.